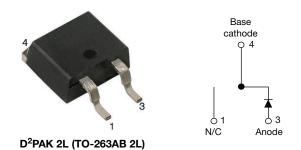
Vishay Semiconductors

Hyperfast Rectifier, 30 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES

30	Ē
3D Models	Applie

SPICE Models

PRIMARY CHARACTERISTICS								
I _{F(AV)}	30 A							
V _R	1200 V							
V _F at I _F at 125 °C	2.1 V							
t _{rr}	26 ns							
T _J max.	175 °C							
Package	D ² PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

FEATURES

- Minimum creepage and clearance distances are 5.2 mm and 5.4 mm respectively
- Hyperfast and optimized Qrr
- Best in class forward voltage drop and switching HALOGEN
 Iosses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets MSL level, per J-Std-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for high frequency converters, both soft switched / resonant.

Specifically designed to improve efficiency of PFC and output rectification stages of EV / HEV battery charging stations, booster stage of solar inverters and UPS applications, these devices are perfectly matched to operate with MOSFETs or high speed IGBTs.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		1200	V						
Average rectified forward current	I _{F(AV)}	T _C = 83 °C, D = 0.50	30							
Non-repetitive peak surge current	I _{FSM}	T_{C} = 83 °C, t_{p} = 10 ms, sine wave	190	A						
Repetitive peak forward current	I _{FRM}	$T_{C} = 45 \text{ °C}, D = 0.50, f = 20 \text{ kHz}$	60							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)										
PARAMETER SYMBOL TEST CONDITIONS				TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	1200	-	-					
Forward voltage	VF	I _F = 30 A	-	2.6	3.3	V				
	v _F	I _F = 30 A, T _J = 125 °C	-	2.1	-					
Poveros loskago ourrent	L	V _R = V _R rated	-	-	50					
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V _R = 200 V	-	17	-	pF				
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH				

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COMPLIANT



VS-E5TX3012S2LHM3



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DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST C	CONDITIONS	MIN.	TYP.	MAX.	UNITS		
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t$	$= 100 \text{ A/}\mu\text{s}, \text{V}_{\text{R}} = 30 \text{ V}$	-	26	-			
Reverse recovery time	t _{rr}	T _J = 25 °C		-	100	-	ns		
		T _J = 125 °C		-	150	-			
Peak recovery current	1	T _J = 25 °C	I _F = 20 A dI _F /dt = 600 A/µs	-	12	-	А		
	I _{RRM}	T _J = 125 °C	$V_{R} = 400 V$	-	22	-			
	Q _{rr}	T _J = 25 °C		-	530	-	nC		
Reverse recovery charge		T _J = 125 °C		-	1650	-			
Reverse recovery time	+	T _J = 25 °C		-	80	-	ns		
nevelse recovery time	t _{rr}	T _J = 125 °C		-	120	-			
Peole recovery ourrept	1	T _J = 25 °C	I _F = 30 A dI _F /dt = 1000 A/µs	-	22	-	А		
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 800 \text{ V}$	-	37	-			
Poverse receiver / oberge	0	T _J = 25 °C]	-	900	-			
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	2400	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.1	°C/W				
Weight			-	2.0	-	g				
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style D ² PAK 2L (TO-263AB 2L)	E5TX3012SH							



VS-E5TX3012S2LHM3

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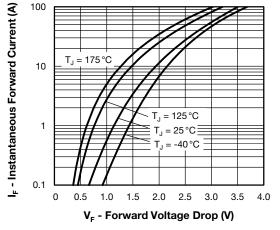


Fig. 1 - Typical Forward Voltage Drop Characteristics

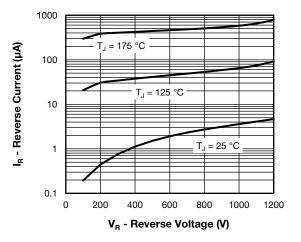


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

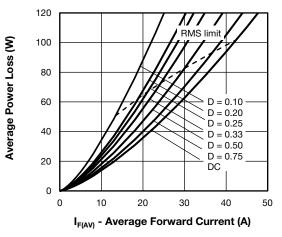


Fig. 5 - Typical Recovery Current vs. dl_F/dt

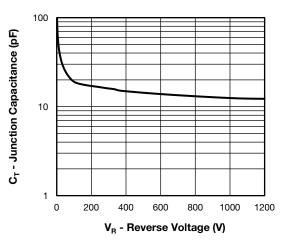


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

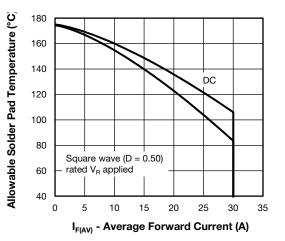


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

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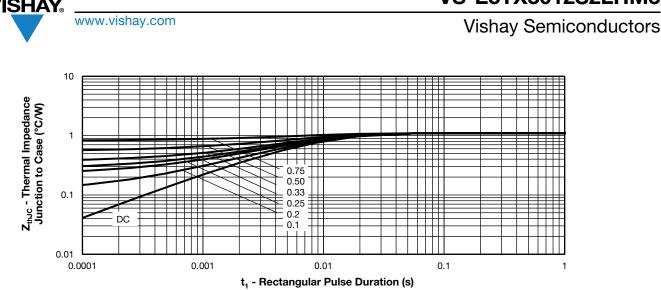


Fig. 6 - Thermal Impedance ZthJC Characteristics

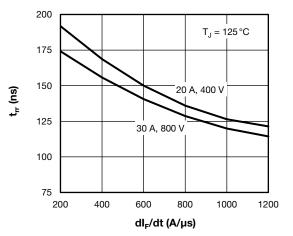


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

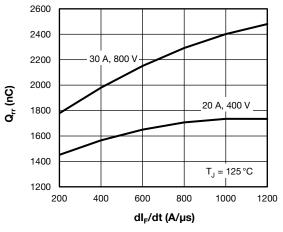


Fig. 8 - Typical Stored Charge vs. dl_F/dt

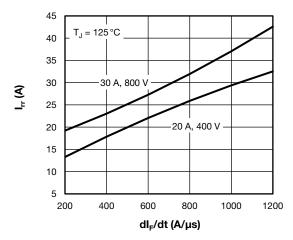


Fig. 9 - Typical Recovery Current vs. dl_F/dt



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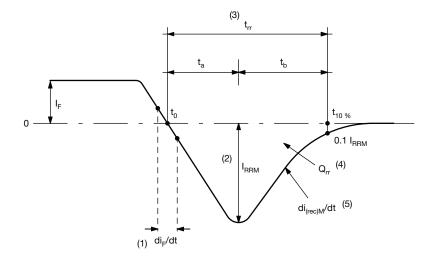


Fig. 10 - Reverse Recovery Waveform and Definitions

Notes

- $^{(1)}~di_{F}/dt$ rate of change of current through zero crossing
- ⁽²⁾ I_{RRM} peak reverse recovery current
- $^{(3)}$ t_{rr} reverse recovery time measured from t₀, crossing point of negative going I_F, to point t_{10%}, 0.1 I_{RRM}
- $^{(4)}~$ Qrr area under curve defined by t_0 and $t_{10\ \%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}



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ORDERING INFORMATION TABLE

Device code	vs-	Е	5	т	x	30	12	S2	L	н	МЗ
	1	2	3	4	5	6	7	8	9	10	(11)
	1 - Vishay Semiconductors product										
	2 - E = single diode										
	3 -										
	 Package: T = D²PAK (TO-262) package 										
	5 -	· X =	hyperfa	st recov	/ery						
	6 -	· Cur	rent rati	ng (30 =	= 30 A)						
	7 -	· Volt	age rati	ng (12 =	= 1200 \	/)					
	8	- S2	= true 2	pin D ² F	PAK						
	 9 - None = tube (50 pieces) • L = tape and reel (left oriented, for D²PAK package) If needed different orientation/packaging, please contact factory 10 - H = AEC-Q101 qualified 										
	11 -		rironmer = halog	•		complia	ant, and	termina	ation lea	d (Pb)-f	ree

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-E5TX3012S2LHM3	800	13" diameter reel							

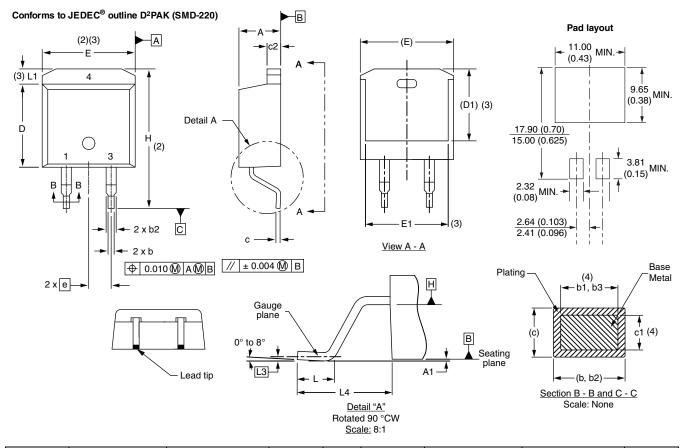
LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?96683						
Part marking information	www.vishay.com/doc?96693						
Packaging information	www.vishay.com/doc?95032						
SPICE model	www.vishay.com/doc?97017						

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D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL		MILLIM	IETERS	INC	HES	NOTES		
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES			
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3		
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3		
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3		
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100) BSC			
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625			
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110			
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3		
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		L3 0.25 BSC		0.010	BSC	
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208			
D	8.51	9.65	0.335	0.380	2									

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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